First Semester Examination
Academic Session 2018/2019

December 2018/January 2019

EEE532 – MICROWAVE CIRCUIT DESIGN

Duration : 2 hours

Please check that this examination paper consists of FIVE (5) pages and appendixes TWELVE (12) pages of printed material before you begin the examination.

Instructions: This question paper consists of **FOUR (4)** questions. Answer **ALL** questions. All questions carry the same marks.

1. In radio frequency and microwave engineering, there are many types of transmission line used to carry high frequency signals. One example of a transmission line is the microstrip circuit.

(a) (i) Sketch a typical microstrip structure complete with labels.

(20 marks)

(ii) What is the transverse propagation mode of a microstrip circuit? Show how the electric field and magnetic field radiate in a microstrip circuit in the sketch in (a) i).

(20 marks)

(iii) Explain the difference between the transverse propagation mode of a microstrip circuit with other types of transverse modes, such as transverse – electric (TE) or transverse – magnetic (TM) modes.

(20 marks)

(b) A microstrip line constructed on FR-4 with microstrip width *w* = 3.058 mm, relative permittivity ε_r = 4.4, microstrip line thickness *t* = 0.1 mm, substrate height *h* = 1.7 mm is terminated by load impedance of 400 Ω. The power at the input terminal is 200 W at *f* = 2.45 GHz. **By using the Pozar's approximation:**

(i) Find the characteristic impedance Z_0 of the *w* = 3.058 mm line.

(10 marks)

(ii) Calculate the characteristic impedance of a quarter wavelength-long line that could be used to match the load and increase the power delivered to the load. State the type of circuit.

(20 marks)

(iii) Find the width of this quarter wave section.

(10 marks)

2. (a) Microstrip coupled line coupler is one of the common couplers used as a quadrature coupler. Coupled lines occur when two transmission lines are close enough in proximity so that energy from one line passes to the other.

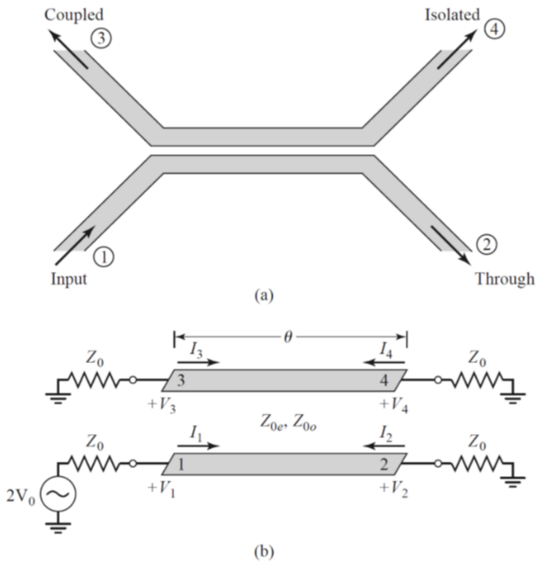

Figure 1: A single-section coupled line coupler (a) Geometry and port designations (b) The schematic circuit

A coupler can be designed with arbitrary coupling such that the input (Port 1) is matched, while Port 4 is isolated, Port 2 is the through port, and Port 3 is the coupled port. **Derive** the appropriate equations to show that the input impedance of a coupled microstrip line can be reduced to $Z_{in} = Z_0$. Insert assumptions where appropriate. Start with:

$$Z_{in} = \frac{V_1}{I_1} = \frac{V_1^e + V_1^o}{I_1^e + I_1^o}$$

(45 marks)

(b) The realization of a microwave circuit can vary according to different requirements and necessities of a certain application. Discuss the difference between Monolithic Microwave Integrated Circuit (MMIC) and Radio Frequency Integrated Circuit (RFIC) and their respective advantages.

(20 marks)

(c) By using Smith Chart, design a shorted stub matching network for a 50 Ω line terminated in a load $Z_L = 20 - j55$ Ω. Perform all the steps required in completing the design.

(35 marks)

3. (a) Referring to a block diagram in Figure 2, design a 2.49 GHz wireless transmitter having the specifications as in Table 1. The information for the components that is required for the design is attached in the Appendix B to I.

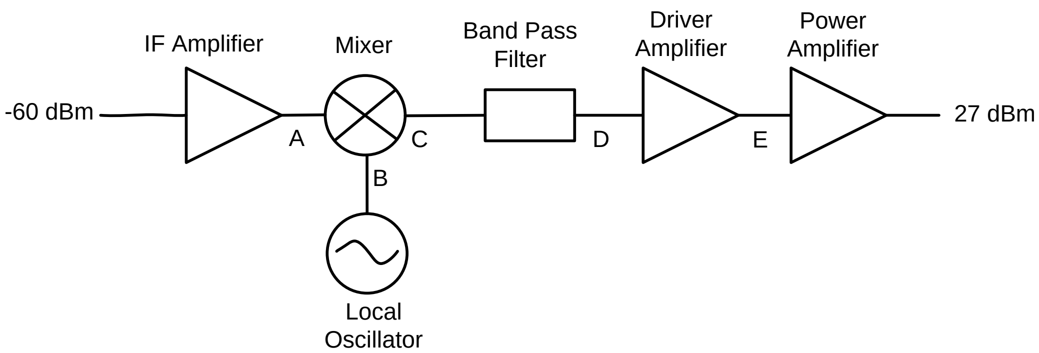

Figure 2

Table 1: Specification for 2.49 GHz wireless transmitter

TX Frequency	IF Frequency	Bandwidth	TX Power
2.49 GHz	140 MHz	40 MHz	26 dBm

(i) Determine the gain of the IF amplifier and power level at point A (assume minimum input power to the mixer RF port is -40 dBm)?

(20 marks)

(ii) What is the frequency of the Local Oscillator and minimum output power of the Local Oscillator at point B?

(20 marks)

(iii) Based on the mixer specification and minimum Local Oscillator drive power, what is the mixer output power at point C?

(20 marks)

(iv) Referring to the datasheet of the Band Pass Filter, what is the power level at point D?

(15 marks)

(v) How many Driver Amplifier are required to drive the power amplifier to deliver 26 dBm?

(15 marks)

(vi) How much gain is required for the Power Amplifier?

(10 marks)

4. The PHEMT ATF 36077 having the S-parameter and noise parameter as in the Appendix A. Design a Low Noise Amplifier operating at 4 GHz. Choose Γ_{in} at C_i and using F_r at 0.4 dB. Microwave laminate having the thickness of 0.813 mm with ε_r 3.38 must be used. The following important formulas may be useful.

(a) Calculate the center of the input noise circle point C_i.

(20 marks)

(b) Calculate the radius of the input noise circle R_i.

(20 marks)

(c) By using the Smith chart, design the input noise figure matching.

(30 marks)

(d) Based on calculated C_i, calculate the load reflection coefficient Γ_L and design the output matching.

(30 marks)

$$C_i = \frac{\Gamma_{opt}}{(1+N_i)}$$

$$Zo \approx \frac{87}{\sqrt{\varepsilon_r + 1.41}} \ln\left(\frac{5.98h}{0.8w+t}\right)$$

$$R_i = \frac{1}{1+N_i}\sqrt{N_i^{\,2} + N_i(1-|\Gamma_{opt}|^2)}$$

$$Ni = \frac{\left[(Fr - F\min)\left|1+\Gamma_{opt}\right|^2\right]}{4\dfrac{R_n}{Z_o}}$$

$$\Gamma_L = \left(S_{22} + \frac{S_{12}S_{21}\Gamma_{in}}{1-S_{11}\Gamma_{in}}\right)^*$$

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APPENDIX A (1/3)

LAMPIRAN A (1/3)

2–18 GHz Ultra Low Noise Pseudomorphic HEMT

Technical Data

ATF-36077

Features

- **PHEMT Technology**
- **Ultra-Low Noise Figure:** 0.5 dB Typical at 12 GHz 0.3 dB Typical at 4 GHz
- **High Associated Gain:** 12 dB Typical at 12 GHz 17 dB Typical at 4 GHz
- **Low Parasitic Ceramic Microstrip Package**
- **Tape-and-Reel Packing Option Available**

Applications

- **12 GHz DBS LNB (Low Noise Block)**
- **4 GHz TVRO LNB (Low Noise Block)**
- **Ultra-Sensitive Low Noise Amplifiers**

Note: 1. See Noise Parameter Table.

Description

Hewlett-Packard's ATF-36077 is an ultra-low-noise Pseudomorphic High Electron Mobility Transistor (PHEMT), packaged in a low parasitic, surface-mountable ceramic package. Properly matched, this transistor will provide typical 12 GHz noise figures of 0.5 dB, or typical 4 GHz noise figures of 0.3 dB. Additionally, the ATF-36077 has very low noise resistance, reducing the sensitivity of noise performance to variations in input impedance match, making the design of broadband low noise amplifiers much easier. The premium sensitivity of the ATF-36077 makes this device the ideal choice for use in the first stage of extremely low noise cascades.

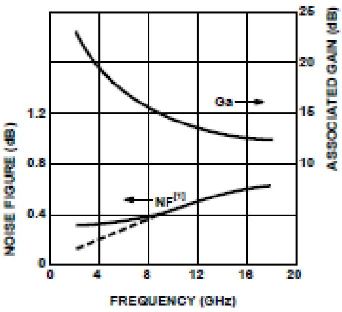
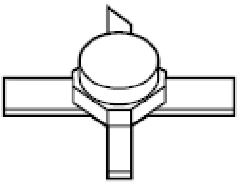
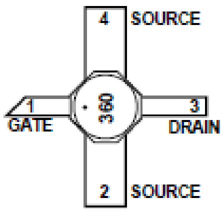


Figure 1. ATF-36077 Optimum Noise Figure and Associated Gain vs. Frequency for V_{DS} = 1.5 V, I_D = 10 mA.

77 Package



Pin Configuration



The repeatable performance and consistency make it appropriate for use in Ku-band Direct Broadcast Satellite (DBS) Television systems, C-band Television Receive Only (TVRO) LNAs, or other low noise amplifiers operating in the 2-18 GHz frequency range.

This GaAs PHEMT device has a nominal 0.2 micron gate length with a total gate periphery (width) of 200 microns. Proven gold based metalization systems and nitride passivation assure rugged, reliable devices.

APPENDIX A (2/3)

LAMPIRAN A (2/3)

ATF-36077 Typical Scattering Parameters,
Common Source, $Z_O = 50\ \Omega$, $V_{DS} = 1.5$ V, $I_D = 10$ mA

Freq. GHz	S_{11} Mag.	S_{11} Ang.	S_{21} dB	S_{21} Mag.	S_{21} Ang.	S_{12} dB	S_{12} Mag.	S_{12} Ang.	S_{22} Mag.	S_{22} Ang.
1.0	0.99	-17	14.00	5.010	163	-36.08	0.016	78	0.60	-14
2.0	0.97	-33	13.81	4.904	147	-30.33	0.030	66	0.59	-28
3.0	0.94	-49	13.53	4.745	132	-27.25	0.043	54	0.57	-41
4.0	0.90	-65	13.17	4.556	116	-25.32	0.054	43	0.55	-54
5.0	0.86	-79	12.78	4.357	102	-24.04	0.063	33	0.53	-66
6.0	0.82	-93	12.39	4.162	88	-23.17	0.069	24	0.50	-78
7.0	0.78	-107	12.00	3.981	75	-22.58	0.074	16	0.48	-89
8.0	0.75	-120	11.64	3.820	62	-22.17	0.078	8	0.46	-99
9.0	0.72	-133	11.32	3.682	49	-21.90	0.080	1	0.44	-109
10.0	0.69	-146	11.04	3.566	37	-21.71	0.082	-6	0.42	-119
11.0	0.66	-159	10.81	3.473	25	-21.57	0.083	-13	0.40	-129
12.0	0.63	-172	10.63	3.401	13	-21.44	0.085	-19	0.38	-139
13.0	0.61	175	10.50	3.349	1	-21.32	0.086	-25	0.37	-149
14.0	0.60	161	10.41	3.315	-12	-21.19	0.087	-32	0.35	-160
15.0	0.58	147	10.36	3.296	-24	-21.04	0.089	-39	0.33	-171
16.0	0.57	131	10.34	3.289	-37	-20.87	0.091	-47	0.31	177
17.0	0.56	114	10.34	3.289	-50	-20.69	0.092	-55	0.29	164
18.0	0.57	97	10.35	3.291	-64	-20.53	0.094	-65	0.26	148

ATF-36077 Typical "Off" Scattering Parameters,
Common Source, $Z_O = 50\ \Omega$, $V_{DS} = 1.5$ V, $I_D = 0$ mA, $V_{GS} = -2$ V

Freq. GHz	S_{11} Mag.	S_{11} Ang.	S_{21} dB	S_{21} Mag.	S_{21} Ang.	S_{21} dB	S_{21} Mag.	S_{21} Ang.	S_{22} Mag.	S_{22} Ang.
11.0	0.96	-139	-14.2	0.19	-43	-14.2	0.19	-43	0.97	-125
12.0	0.95	-152	-14.0	0.20	-56	-14.0	0.20	-56	0.97	-137
13.0	0.94	-166	-13.8	0.20	-69	-13.8	0.20	-68	0.96	-149

APPENDIX A (3/3)

LAMPIRAN A (3/3)

ATF-36077 Typical Noise Parameters,

Common Source, $Z_O = 50\,\Omega$, $V_{DS} = 1.5$ V, $I_D = 10$ mA

Freq. GHz	F_{min}[1] dB	Γ_{opt} Mag.	Γ_{opt} Ang.	R_n/Z_o -
1	0.30	0.95	12	0.40
2	0.30	0.90	25	0.20
4	0.30	0.81	51	0.17
6	0.30	0.73	76	0.13
8	0.37	0.66	102	0.09
10	0.44	0.60	129	0.05
12	0.50	0.54	156	0.03
14	0.56	0.48	-174	0.02
16	0.61	0.43	-139	0.05
18	0.65	0.39	-100	0.09

Note:
1. The F_{min} values at 2, 4, and 6 GHz have been adjusted to reflect expected circuit losses that will be encountered when matching to the optimum reflection coefficient (Γ_{opt}) at these frequencies. The theoretical F_{min} values for these frequencies are: 0.10 dB at 2 GHz, 0.20 dB at 4 GHz, and 0.29 dB at 6 GHz. Noise parameters are derived from associated s parameters, packaged device measurements at 12 GHz, and die level measurements from 6 to 18 GHz.

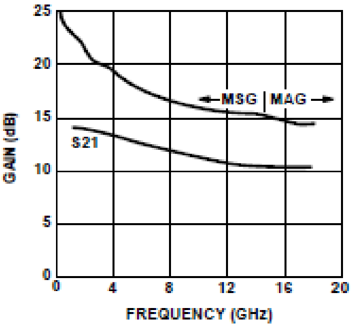
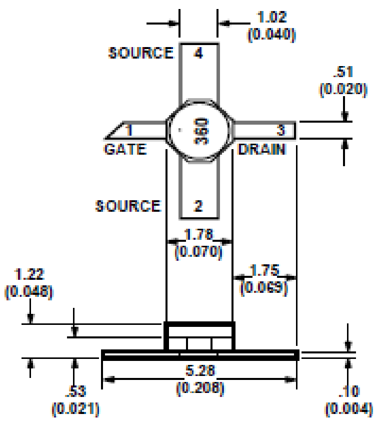


Figure 2. Maximum Available Gain, Maximum Stable Gain and Insertion Power Gain vs. Frequency. $V_{DS} = 1.5$ V, $I_D = 10$ mA.

77 Package Dimensions



TYPICAL DIMENSIONS ARE IN MILLIMETERS (INCHES).

Part Number Ordering Information

Part Number	No. of Devices	Container
ATF-36077-TR1[2]	1000	7" Reel
ATF-36077-STR	10	strip

Note:
2. For more information, see "Tape and Reel Packaging for Semiconductor Devices," in "Communications Components" Designer's Catalog.

APPENDIX B

LAMPIRAN B

MIXER

SPECIFICATIONS

V_S = 5 V, I_S = 100 mA, T_A = 25°C, f_{RF} = 2535 MHz, f_{LO} = 2738 MHz, LO power = 0 dBm, Z_O = 50 Ω, unless otherwise noted.

Table 2.

Parameter	Test Conditions/Comments	Min	Typ	Max	Unit
RF INPUT INTERFACE					
Return Loss	Tunable to >20 dB over a limited bandwidth		16		dB
Input Impedance			50		Ω
RF Frequency Range		2300		2900	MHz
OUTPUT INTERFACE					
Output Impedance	Differential impedance, f = 200 MHz		33‖-0.3		Ω‖pF
IF Frequency Range		dc		450	MHz
DC Bias Voltage[1]	Externally generated	3.3	5.0	5.5	V
LO INTERFACE					
LO Power		−6	0	+10	dBm
Return Loss			15		dB
Input Impedance			50		Ω
LO Frequency Range		2330		3350	MHz
POWER-DOWN (PWDN) INTERFACE[2]					
PWDN Threshold			1.0		V
Logic 0 Level				0.4	V
Logic 1 Level		1.4			V
PWDN Response Time	Device enabled, IF output to 90% of its final level		160		ns
	Device disabled, supply current <5 mA		220		ns
PWDN Input Bias Current	Device enabled		0.0		μA
	Device disabled		70		μA

[1] Apply the supply voltage from the external circuit through the choke inductors.
[2] The PWDN function is intended for use with $V_S \leq 3.6$ V only.

APPENDIX C

LAMPIRAN C

5 V PERFORMANCE

V_S = 5 V, I_S = 100 mA, T_A = 25°C, f_{RF} = 2535 MHz, f_{LO} = 2738 MHz, LO power = 0 dBm, VGS0 = VGS1 = 0 V, and Z_O = 50 Ω, unless otherwise noted.

Table 3.

Parameter	Test Conditions/Comments	Min	Typ	Max	Unit
DYNAMIC PERFORMANCE					
Power Conversion Loss	Including 1:1 IF port transformer and PCB loss		7.7		dB
SSB Noise Figure			7.6		dB
Input Third-Order Intercept (IIP3)	f_{RF1} = 2534.5 MHz, f_{RF2} = 2535.5 MHz, f_{LO} = 2738 MHz, each RF tone at 0 dBm		31		dBm
Input Second-Order Intercept (IIP2)	f_{RF1} = 2535 MHz, f_{RF2} = 2585 MHz, f_{LO} = 2738 MHz, each RF tone at 0 dBm		62		dBm
Input 1 dB Compression Point (IP1dB)[1]	Exceeding 20 dBm RF power results in damage to the device		25		dBm
LO-to-IF Leakage	Unfiltered IF output		−22		dBm
LO-to-RF Leakage			−32		dBm
RF-to-IF Isolation			−44		dBc
IF/2 Spurious	−10 dBm input power		−61		dBc
IF/3 Spurious	−10 dBm input power		−70		dBc
POWER SUPPLY					
Positive Supply Voltage		4.5	5	5.5	V
Quiescent Current	V_S = 5 V		100		mA

[1] Exceeding 20 dBm RF power results in damage to the device.

3.3 V PERFORMANCE

V_S = 3.3 V, I_S = 60 mA, T_A = 25°C, f_{RF} = 2535 MHz, f_{LO} = 2738 MHz, LO power = 0 dBm, R9 = 226 Ω, VGS0 = VGS1 = 0 V, and Z_O = 50 Ω, unless otherwise noted.

Table 4.

Parameter	Test Conditions/Comments	Min	Typ	Max	Unit
DYNAMIC PERFORMANCE					
Power Conversion Loss	Including 1:1 IF port transformer and PCB loss		7.4		dB
SSB Noise Figure			6.8		dB
Input Third-Order Intercept (IIP3)	f_{RF1} = 2534.5 MHz, f_{RF2} = 2535.5 MHz, f_{LO} = 2738 MHz, each RF tone at 0 dBm		26		dBm
Input Second-Order Intercept (IIP2)	f_{RF1} = 2535 MHz, f_{RF2} = 2585 MHz, f_{LO} = 2738 MHz, each RF tone at 0 dBm		56		dBm
POWER SUPPLY					
Positive Supply Voltage			3.3		V
Quiescent Current	V_S = 5 V		60		mA

APPENDIX D

LAMPIRAN D

OSCILLATOR

ANALOG DEVICES

HMC385LP4 / 385LP4E

v02.0705

MMIC VCO w/ BUFFER AMPLIFIER, 2.25 - 2.5 GHz

RoHS✓ EARTH FRIENDLY

Typical Applications

Low noise MMIC VCO w/Buffer Amplifier for:

- Wireless Infrastructure
- Industrial Controls
- Test Equipment
- Military

Features

Pout: +4.5 dBm

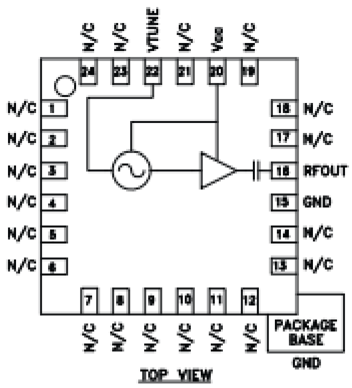
Phase Noise: -115 dBc/Hz @100 KHz

No External Resonator Needed

Single Supply: 3V @ 35 mA

QFN Leadless SMT Package, 16 mm²

Functional Diagram



General Description

The HMC385LP4 & HMC385LP4E are GaAs InGaP Heterojunction Bipolar Transistor (HBT) MMIC VCOs with integrated resonators, negative resistance devices, varactor diodes, and buffer amplifiers. Covering 2.25 to 2.5 GHz, the VCO's phase noise performance is excellent over temperature, shock, vibration and process due to the oscillator's monolithic structure. Power output is 4.5 dBm typical from a single supply of 3V @ 35mA. The voltage controlled oscillator is packaged in a low cost leadless QFN 4x4 mm surface mount package.

Electrical Specifications, T_A = +25° C, Vcc = +3V

Parameter	Min.	Typ.	Max.	Units
Frequency Range		2.25 - 2.5		GHz
Power Output	1.5	4.5		dBm
SSB Phase Noise @ 100 kHz Offset, Vtune= +5V @ RF Output		-115		dBc/Hz
Tune Voltage (Vtune)	0		10	V
Supply Current (Icc) (Vcc = +3.0V)		35		mA
Tune Port Leakage Current			10	µA
Output Return Loss		9		dB
Harmonics 2nd 3rd		 -7 -23		 dBc dBc
Pulling (into a 2.0:1 VSWR)		2.0		MHz pp
Pushing @ Vtune= +5V		-2		MHz/V
Frequency Drift Rate		0.25		MHz/°C

APPENDIX E

LAMPIRAN E

AMPLIFIERS

ANALOG DEVICES

HMC680LP4 / 680LP4E

v03.0609

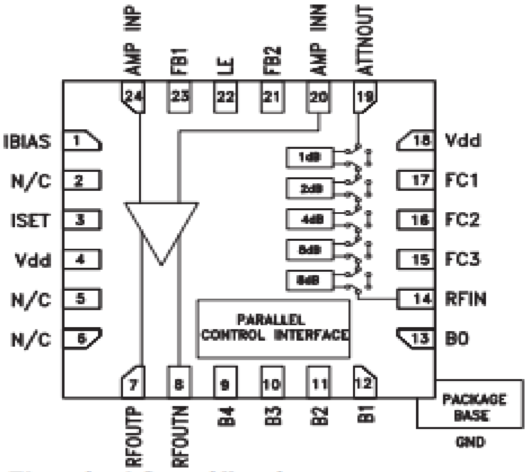
BiCMOS MMIC 5-BIT DIGITAL VARIABLE GAIN AMPLIFIER, 30 - 400 MHz

Typical Applications

The HMC680LP4(E) is ideal for:

- Cellular/3G Infrastructure
- WiBro / WiMAX / 4G
- Microwave Radio & VSAT
- Test Equipment and Sensors
- IF & RF Applications

Functional Diagram



Features

TTL/CMOS compatible parallel or latched parallel control interface

High Output IP3: +40 dBm (At all gain settings)

Low Noise Figure: 5 dB

Wide Gain Control Range: 23 dB

24 Lead 4x4 mm SMT Package: 16 mm²

Excellent State & Step Accuracy (±0.05 dB)

General Description

The HMC680LP4(E) is a digitally controlled variable gain amplifier which operates from 30 to 400 MHz, and can be programmed to provide -4 dB to +19 dB of gain, in 1 dB steps. The HMC680LP4(E) delivers noise figure of 5 dB in its maximum gain state, with output IP3 of up to +40 dBm in any state. This high linearity DVGA also provides a differential RF output which can be used to interface directly with SAW filters in Tx and Rx applications, and with digital to analog converters in Rx chains. The HMC680LP4(E) is housed in a RoHS compliant 4x4 mm QFN leadless package, and is CMOS/ TTL compatible.

Electrical Specifications, T_A = +25° C, 50 Ohm System, Vdd = +5V

Parameter		Min.	Typ.	Max.	Units
Frequency Range			30 - 400		MHz
Gain (Maximum Gain State)		17	19		dB
Gain Control Range			23		dB
Input Return Loss			12		dB
Output Return Loss			13		dB
Gain Accuracy: (Referenced to Maximum Gain State) All Gain States		± (0.15 + 3% of Gain Setting) Max.			dB
Output Power for 1dB Compression		23	25		dBm
Output Third Order Intercept Point (Two-Tone Output Power= +5 dBm Each Tone) [1]			40		dBm
Output Second Order Intercept Point (Two-Tone Output Power= +5 dBm Each Tone) [1]			65		dBm
Harmonics	2nd Order 3rd Order		70 75		dBc dBc
Step Accuracy (Referenced to Maximum Gain State)			±0.2		dB
Noise Figure (max gain state)			5		dB
Switching Characteristics	tRise, tFall (10/90% RF) tON, tOFF (50% CTL to 10/90% RF)		11 13		ns ns
Control Supply Current Idd			4	5	mA
Amp Supply Current (RFOUTP)			122	135	mA
Amp Supply Current (RFOUTN)			122	135	mA

[1] Test frequency 50 MHz

APPENDIX F

LAMPIRAN F

ANALOG DEVICES

2.3 GHz to 4.0 GHz ¼ Watt RF Driver Amplifier

Data Sheet **ADL5321**

FEATURES

Operation: 2.3 GHz to 4.0 GHz
Gain of 14.0 dB at 2.6 GHz
OIP3 of 41.0 dBm at 2.6 GHz
P1dB of 25.7 dBm at 2.6 GHz
Noise figure: 4.0 dB at 2.6 GHz
Power supply voltage: 3.3 V to 5 V
Power supply current: 37 mA to 90 mA
Dynamically adjustable bias
No bias resistor required
Thermally efficient, MSL-1 rated SOT-89 package
Operating temperature range: −40°C to +105°C
ESD rating of ±2 kV (Class 3A)

APPLICATIONS

Wireless infrastructure
Automated test equipment
ISM/AMR applications

FUNCTIONAL BLOCK DIAGRAM

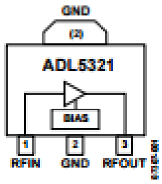


Figure 1.

GENERAL DESCRIPTION

The ADL5321 incorporates a dynamically adjustable biasing circuit that allows for the customization of OIP3 and P1dB performance from 3.3 V to 5 V without the need for an external bias resistor. This feature gives the designer the ability to tailor driver amplifier performance to the specific needs of the design. This feature also creates the opportunity for dynamic biasing of the driver amplifier, where a variable supply is used to allow for full 5 V biasing under large signal conditions and then can reduce the supply voltage when signal levels are smaller and lower power consumption is desirable. This scalability reduces the need to evaluate and inventory multiple driver amplifiers for different output power requirements from 22 dBm to 26 dBm output power levels.

The ADL5321 is also rated to operate across the wide temperature range of −40°C to +105°C for reliable performance in designs that experience higher temperatures, such as power amplifiers. The ¼ watt driver amplifier covers the 2.3 GHz to 4.0 GHz wide frequency range and only requires a few external components to be tuned to a specific band within that wide range. This high performance, broadband RF driver amplifier is well suited for a variety of wired and wireless applications including cellular infrastructure, ISM band power amplifiers, defense equipment, and instrumentation equipment. A fully populated evaluation board is available.

The ADL5321 also delivers excellent adjacent channel leakage ratio (ACLR) vs. P_{OUT}. For output powers up to 10 dBm rms, the ADL5321 adds very little distortion to the output spectrum. At 2.6 GHz, the ACLR is −59 dB and a relative constellation error of −46.6 dB (<0.5% EVM) at an output power of 10 dBm rms.

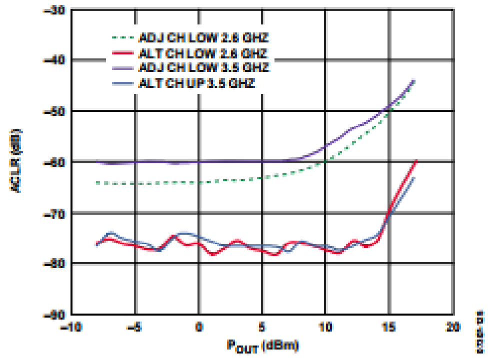


Figure 2. WiMAX 64 QAM, 10 MHz Bandwidth, Single Carrier

APPENDIX G

LAMPIRAN G

ADL5321 Data Sheet

TYPICAL SCATTERING PARAMETERS

VCC = 5 V and T_A = 25°C; the effects of the test fixture have been de-embedded up to the pins of the device.

Table 2.

Frequency (MHz)	S11		S21		S12		S22	
	Magnitude (dB)	Angle (°)	Magnitude (dB)	Angle (°)	Magnitude (dB)	Angle (°)	Magnitude (dB)	Angle (°)
2400	−4.54	129.60	11.90	21.92	−26.72	−33.83	−8.18	−166.39
2450	−4.65	126.65	11.89	18.30	-26.63	−36.64	−8.27	−169.02
2500	−4.79	123.62	11.88	14.57	-26.55	−39.62	−8.37	−171.83
2550	−4.92	120.44	11.87	10.68	−26.48	−42.70	−8.45	−175.32
2600	−5.04	117.31	11.85	6.80	−26.42	−45.95	−8.44	−179.11
2650	−5.17	114.43	11.83	2.90	−26.37	−49.25	−8.39	177.31
2700	−5.33	111.78	11.80	−1.06	−26.34	−52.65	−8.33	173.43
2750	−5.50	109.21	11.77	−5.17	−26.31	−56.16	−8.15	169.22
2800	−5.70	106.84	11.74	−9.36	−26.30	−59.84	−7.90	165.46
2850	−5.94	104.85	11.71	−13.64	−26.30	−63.64	−7.63	161.87
2900	−6.25	103.23	11.66	−18.05	−26.31	−67.63	−7.31	158.01
2950	−6.61	101.91	11.62	−22.58	−26.34	−71.77	−6.88	154.58
3000	−7.03	101.06	11.56	−27.18	−26.37	−76.13	−6.44	151.64
3050	−7.53	100.92	11.50	−31.98	−26.44	−80.76	−6.00	148.53
3100	−8.12	101.82	11.40	−36.95	−26.55	−85.61	−5.53	145.65
3150	−8.78	104.04	11.29	−42.09	−26.68	−90.69	−5.03	143.14
3200	−9.47	107.91	11.15	−47.34	−26.85	−95.96	−4.56	140.74
3250	−10.07	113.72	10.97	−52.74	−27.06	−101.50	−4.08	138.36
3300	−10.45	121.55	10.76	−58.29	−27.32	−107.30	−3.61	136.16
3350	−10.45	130.87	10.49	−63.95	−27.65	−113.32	−3.19	133.97
3400	−10.02	140.04	10.17	−69.56	−28.05	−119.45	−2.80	131.77
3450	−9.25	147.61	9.80	−75.16	−28.49	−125.70	−2.43	129.85
3500	−8.28	153.06	9.39	−80.70	−29.00	−132.04	−2.13	128.08
3550	−7.27	156.76	8.92	−86.04	−29.58	−138.45	−1.89	126.22
3600	−6.34	159.01	8.39	−91.20	−30.20	−144.79	−1.66	124.51
3650	−5.51	160.11	7.83	−96.07	−30.88	−151.12	−1.48	123.23
3700	−4.78	160.43	7.26	−100.64	−31.57	−157.36	−1.37	122.16
3750	−4.14	160.36	6.66	−104.97	−32.29	−163.69	−1.27	121.07
3800	−3.60	160.07	6.04	−108.96	−33.02	−170.01	−1.19	120.25
3850	−3.16	159.62	5.43	−112.61	−33.74	−176.34	−1.14	119.79
3900	−2.78	158.95	4.82	−116.07	−34.44	177.21	−1.12	119.31
3950	−2.45	158.24	4.20	−119.27	−35.12	170.60	−1.10	118.94
4000	−2.17	157.64	3.60	−122.18	−35.74	163.89	−1.09	118.86

APPENDIX H

LAMPIRAN H

ANALOG DEVICES

HMC414MS8G / 414MS8GE

v04.0607

RoHS✓ EARTH FRIENDLY

GaAs InGaP HBT MMIC POWER AMPLIFIER, 2.2 - 2.8 GHz

Typical Applications

This amplifier is ideal for use as a power amplifier for 2.2 - 2.7 GHz applications:

- BLUETOOTH
- MMDS

Features

Gain: 20 dB

Saturated Power: +30 dBm

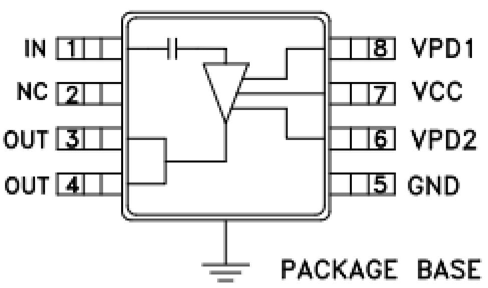
32% PAE

Supply Voltage: +2.75V to +5V

Power Down Capability

Low External Part Count

Functional Diagram



General Description

The HMC414MS8G & HMC414MS8GE are high efficiency GaAs InGaP Heterojunction Bipolar Transistor (HBT) MMIC Power amplifiers which operate between 2.2 and 2.8 GHz. The amplifier is packaged in a low cost, surface mount 8 leaded package with an exposed base for improved RF and thermal performance. With a minimum of external components, the amplifier provides 20 dB of gain, +30 dBm of saturated power at 32% PAE from a +5V supply voltage. The amplifier can also operate with a 3.6V supply. Vpd can be used for full power down or RF output power/ current control.

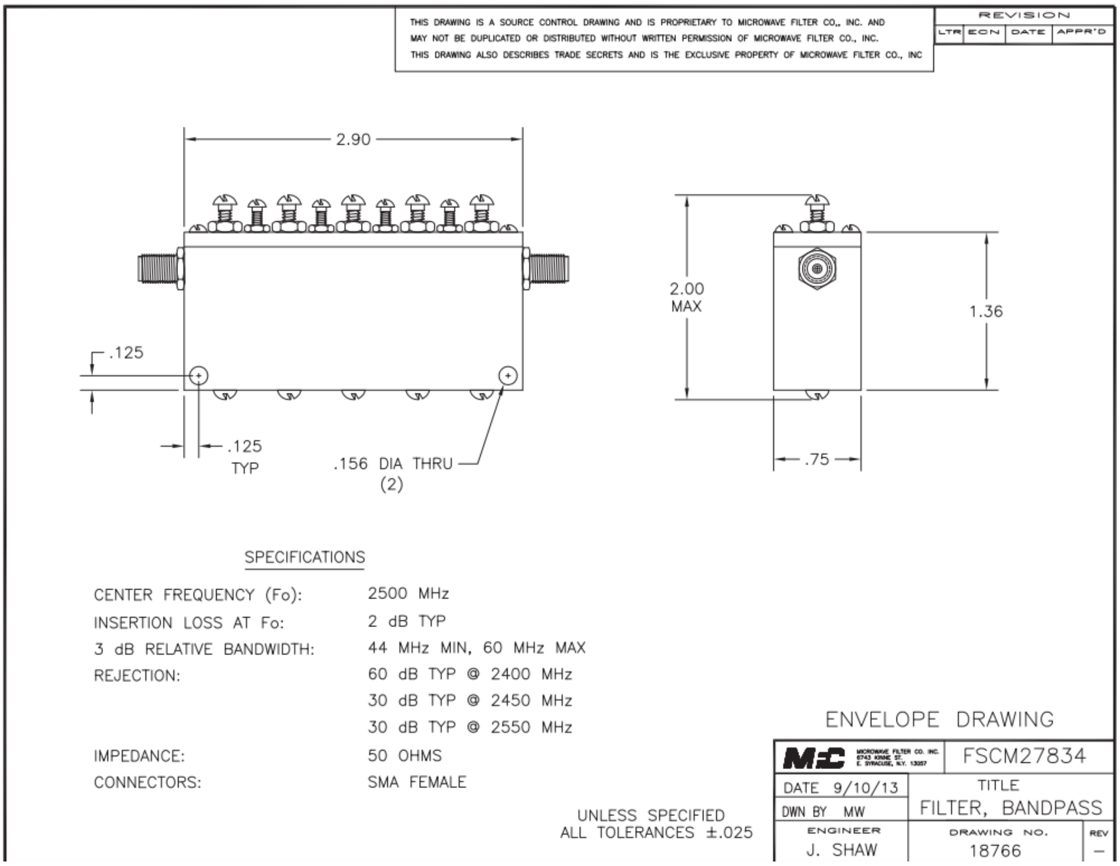
Electrical Specifications, T_A = +25° C, As a Function of Vs, Vpd = 3.6V

Parameter		Vs = 3.6V			Vs = 5V			
		Min.	Typ.	Max.	Min.	Typ.	Max.	Units
Frequency Range			2.2 - 2.8			2.2 - 2.8		GHz
Gain		17	20	25	17	20	25	dB
Gain Variation Over Temperature			0.03	0.04		0.03	0.04	dB/ °C
Input Return Loss			8			8		dB
Output Return Loss			9			9		dB
Output Power for 1 dB Compression (P1dB)		21	25		23	27		dBm
Saturated Output Power (Psat)			27			30		dBm
Output Third Order Intercept (IP3)		30	35		35	39		dBm
Noise Figure			6.5			7.0		dB
Supply Current (Icq)	Vpd = 0V / 3.6V		0.002 / 240			0.002 / 300		mA
Control Current (Ipd)	Vpd = 3.6V		7			7		mA
Switching Speed	tON, tOFF		45			45		ns

APPENDIX I

LAMPIRAN I

FILTER



Course Outcomes (CO) – Programme Outcomes (PO) Mapping
Pemetaan Hasil Pembelajaran Kursus – Hasil Program

Questions ***Soalan***	**CO**	**PO**
1	1	2
2	2	3
3	2	3
4	2	3
5		
6		